2SC3356

NPN Silicon Epitaxial Planar Transistor

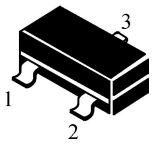
for microwave low noise amplifier at VHF, UHF and CATV band

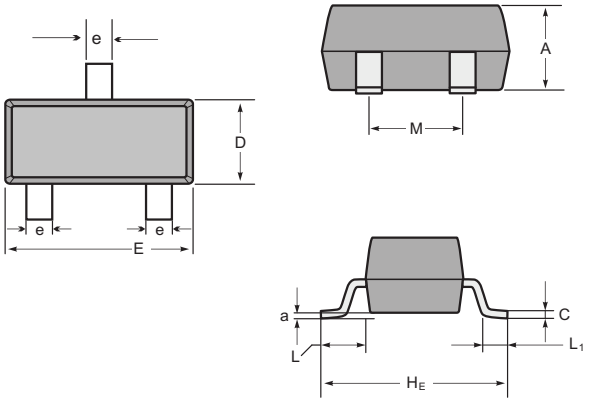
The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.

Marking : R5

SOT—23

1. BASE
2. EMITTER
3. COLLECTOR





SOT-23 mechanical data

UNIT		A	C	D	E	H_E	e	M	L	L_1	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V_{CEO}	12	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	- 65 to + 150	°C

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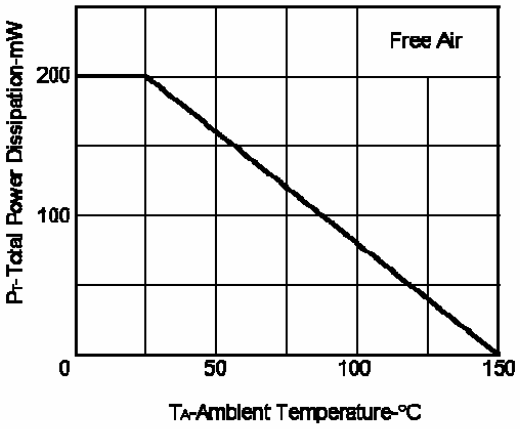
Characteristics (T_a = 25°C)

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 10 V, I_C = 20 mA	Current Gain Group	Q R S	h_{FE} h_{FE} h_{FE}	50 80 125	- - -	100 160 250	- - -
Collector Cutoff Current at V_{CB} = 10 V			I_{CBO}	-	-	1	µA
Emitter Cutoff Current at V_{EB} = 1 V			I_{EBO}	-	-	1	µA
Gain Bandwidth Product at V_{CE} = 10 V, I_C = 20 mA			f_T	-	7	-	GHz
Feed-Back Capacitance at V_{CB} = 10 V, f = 1 MHz			C_{re} [1)]	-	0.55	1	pF
Noise Figure at V_{CE} = 10 V, I_C = 7 mA, f = 1 GHz			NF	-	1.1	2	dB

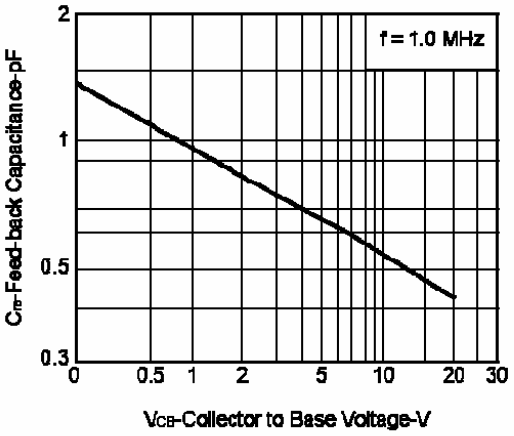
[1)] The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

RATING AND CHARACTERISTIC CURVES (2SC3356)

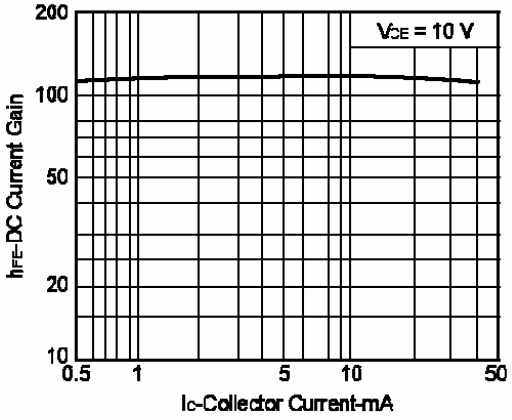
TOTAL POWER DISSIPATION vs.
AMBIENT TEMPERATURE



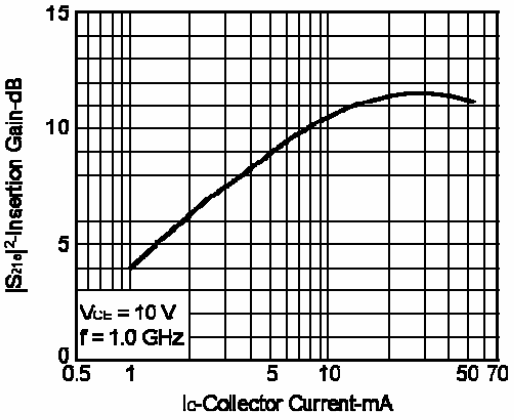
FEED-BACK CAPACITANCE vs.
COLLECTOR TO BASE VOLTAGE



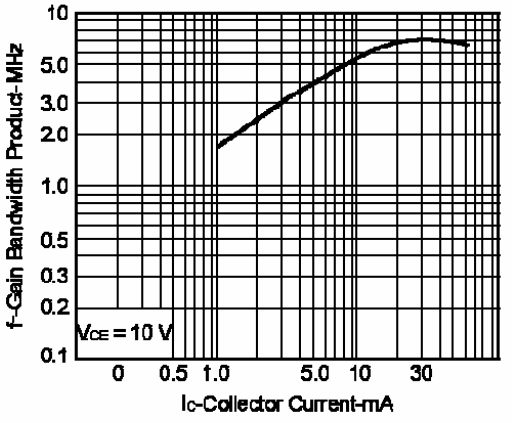
DC CURRENT GAIN vs.
COLLECTOR CURRENT



INSERTION GAIN vs.
COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs.
COLLECTOR CURRENT



INSERTION GAIN, MAXIMUM GAIN
vs. FREQUENCY